

Vishay Semiconductors

Phase Control Thyristors (Stud Version), 110 A



PRIMARY CHARACTERISTICS			
I _{T(AV)}	110 A		
V_{DRM}/V_{RRM}	400 V, 800 V, 1200 V		
V _{TM}	1.57 V		
I _{GT}	80 mA		
TJ	-40 °C to +140 °C		
Package	TO-94 (TO-209AC)		
Circuit configuration Single SCR			

FEATURES





• Hermetic ceramic housing

Designed and qualified for industrial level

ROHS

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		110	A		
I _{T(AV)}	T _C	90	°C		
I _{T(RMS)}		172			
I _{TSM}	50 Hz	2080	Α		
	60 Hz	2180			
I ² t	50 Hz	21.7	kA ² s		
1-1	60 Hz	19.8	KA-S		
V _{DRM} /V _{RRM}		400 to 1200	V		
tq	Typical	110	μs		
T _J		-40 to +140	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA				
VO 440DI	40	400	500					
VS-110RKI VS-111RKI	80	800	900	20				
	120	1200	1300					



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ABSOLUTE MAXIMUM RATINGS	5					
PARAMETER	SYMBOL		TEST CON	IDITIONS	VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	180° condu	ction, half sine v	wave	110	Α
at case temperature	.(,				90	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 83 °C	case temperate	ure	172	
		t = 10 ms	No voltage		2080	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		2180	A - kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		1750	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1830	
Maximum I ² t for fusing		t = 10 ms	t = 10 ms No voltage	initial $T_J = T_J$ maximum	21.7	
	l ² t	t = 8.3 ms	reapplied		19.8	
		t = 10 ms	100 % V _{RRM}		15.3	
		t = 8.3 ms	reapplied		14.0	
Maximum I ² √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied		217	kA ² √	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.82	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.02	V	
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum		2.16	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.70	11152	
Maximum on-state voltage	V_{TM}	$I_{pk} = 350 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$		1.57	V	
Maximum holding current	I _H			V registive lead	200	mA
Typical latching current	ΙL	T _J = 25 °C, anode supply 6 V resistive load		400	mA	

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	300	A/μs		
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}$, $T_J = 25 °C$	1			
Typical turn-off time	tq	$I_{TM} = 50 \text{ A}$, $T_J = T_J$ maximum, $dI/dt = -5 \text{ A}/\mu \text{s}$ $V_R = 50 \text{ V}$, $dV/dt = 20 \text{ V}/\mu \text{s}$, gate $0 \text{ V} 25 \Omega$	110	μs		

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs		
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum rated V_{DRM}/V_{RRM} applied	20	mA		



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TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
PANAMETER	STINIBUL			TYP.	MAX.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	$t_p \leq 5 \ ms$	1	2	W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	3	.0	VV
Maximum peak positive gate current	I _{GM}			3	.0	Α
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum,	$t_p \leq 5 \ ms$	20		V
Maximum peak negative gate voltage	- V _{GM}				10	
		T _J = - 40 °C		180	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger/current/voltage are the lowest value which will	80	120	mA
		T _J = 140 °C		40	-	
		T _J = - 40 °C	trigger all units 12 V anode	2.5 -		
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	to cathode applied	1.6	2	V
	T _J = 140 °C			1	-	
DC gate current not to trigger	I_{GD}		Maximum gate current/	6	.0	mA
DC gate voltage not to trigger	V_{GD}	voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied		0.:	25	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	T_J		-40 to +140	°C	
Maximum storage temperature range	T _{Stg}		-40 to +150	C	
Maximum thermal resistance, junction to case	R _{thJC}	R _{thJC} DC operation		K/W	
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.1	7 ~~~	
Mounting toyour 1100/		Non-lubricated threads	15.5 (137)	N⋅m	
Mounting torque, ± 10 %		Lubricated threads	14 (120)	(lbf·in)	
Approximate weight			130	g	
Case style		See dimensions - link at the end of datasheet TO-94 (TO		209AC)	

△R _{thJC} CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS			
180°	0.043	0.031					
120°	0.052	0.053					
90°	0.066	0.071	$T_J = T_J$ maximum	K/W			
60°	0.096	0.101					
30°	0.167	0.169					

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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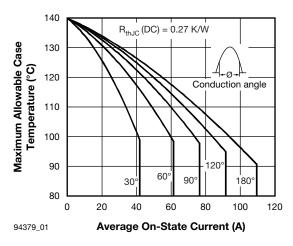


Fig. 1 - Current Ratings Characteristics

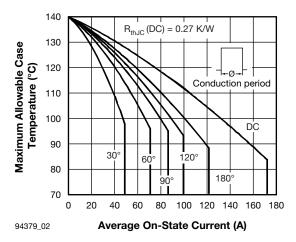
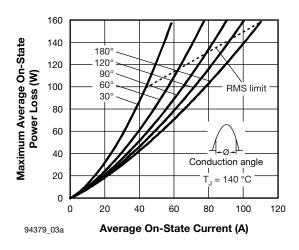


Fig. 2 - Current Ratings Characteristics



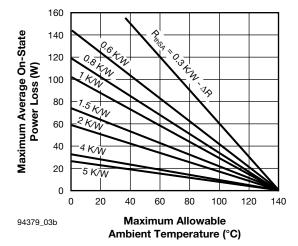
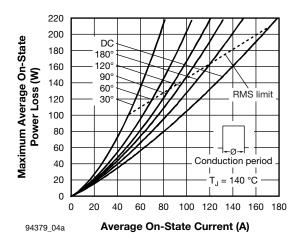


Fig. 3 - On-State Power Loss Characteristics



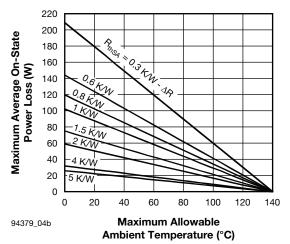


Fig. 4 - On-State Power Loss Characteristics

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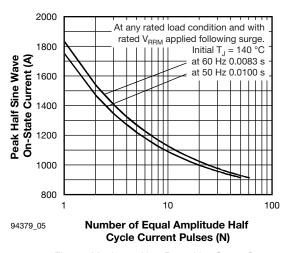


Fig. 5 - Maximum Non-Repetitive Surge Current

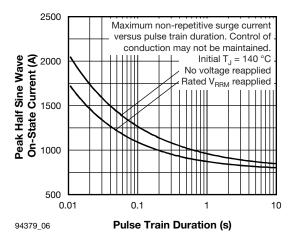


Fig. 6 - Maximum Non-Repetitive Surge Current

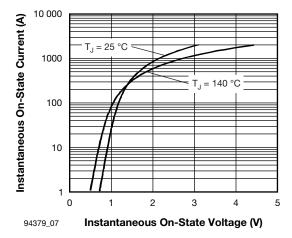


Fig. 7 - On-State Voltage Drop Characteristics

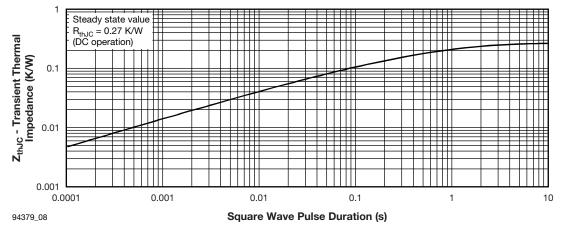


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic

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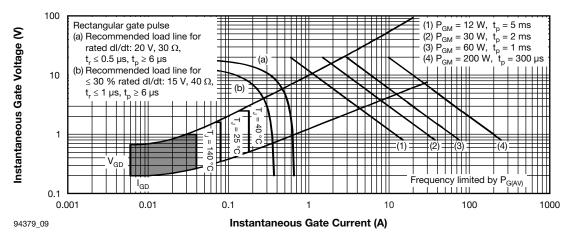
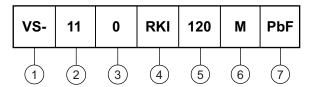


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- **2** I_{T(AV)} rated average output current (rounded/10)
- 0 = eyelet terminals (gate and auxiliary cathode leads)
 - 1 = fast-on terminals (gate and auxiliary cathode leads)
- 4 Thyristor
- Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
- 6 • None = stud base1/2"-20UNF-2A threads
 - M = stud base metric threads M12 x 1.75 E 6
- 7 None = standard production
 - PbF = lead (Pb)-free

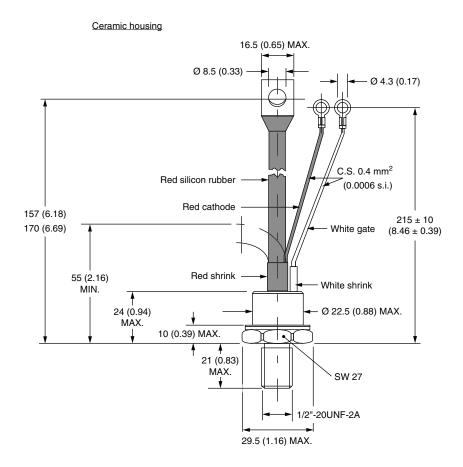
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95003		

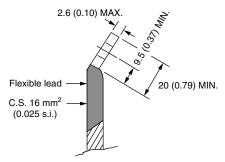


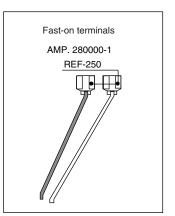
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TO-209AC (TO-94) for 110RKI and 111RKI Series

DIMENSIONS in millimeters (inches)







Note

• For metric device: M12 x 1.75 contact factory



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